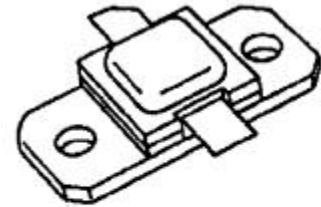


**RF & MICROWAVE TRANSISTORS  
TELEMETRY APPLICATIONS**

**Features**

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- ∞:1 VSWR CAPABILITY AT RATED CONDITIONS
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- P<sub>OUT</sub> = 18 W MINIMUM WITH G<sub>P</sub> = 6.5 dB GAIN MINIMUM
- COMMON BASE CONFIGURATION



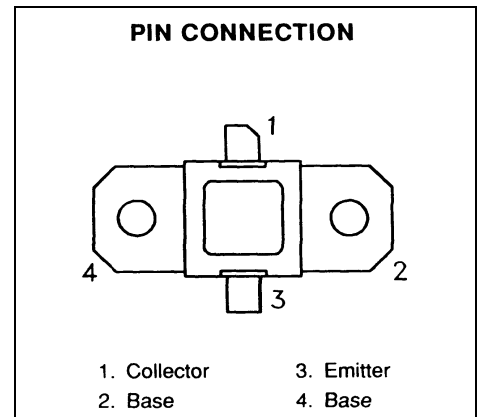
.400 x .400 2L flanged (M214)  
hermetically sealed

**DESCRIPTION:**

The AM82223-018 is a common base, silicon NPN bipolar transistor designed for high gain and efficiency in hi-rel aerospace telemetry applications in the 2.2-2.3 GHz frequency range.

It incorporates internal input and output impedance matching structures along with a rugged, emitter-site ballasted overlay die geometry capable of withstanding ∞:1 load mismatch at any phase angle under full rated operating conditions..

The AM82223-018 is provided in the industry-standard AMPAC™ metal/ceramic hermetic package.



**ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)**

Symbol	Parameter	Value	Unit
P <sub>DISS</sub>	Power Dissipation	58.3	W
I <sub>C</sub>	Device Current*	3.0	A
V <sub>CC</sub>	Collector-Supply Voltage*	28	V
T <sub>J</sub>	Junction Temperature	200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +200	°C

**Thermal Data**

R <sub>TH(J-C)</sub>	Junction-case Thermal Resistance	3.0	°C/W
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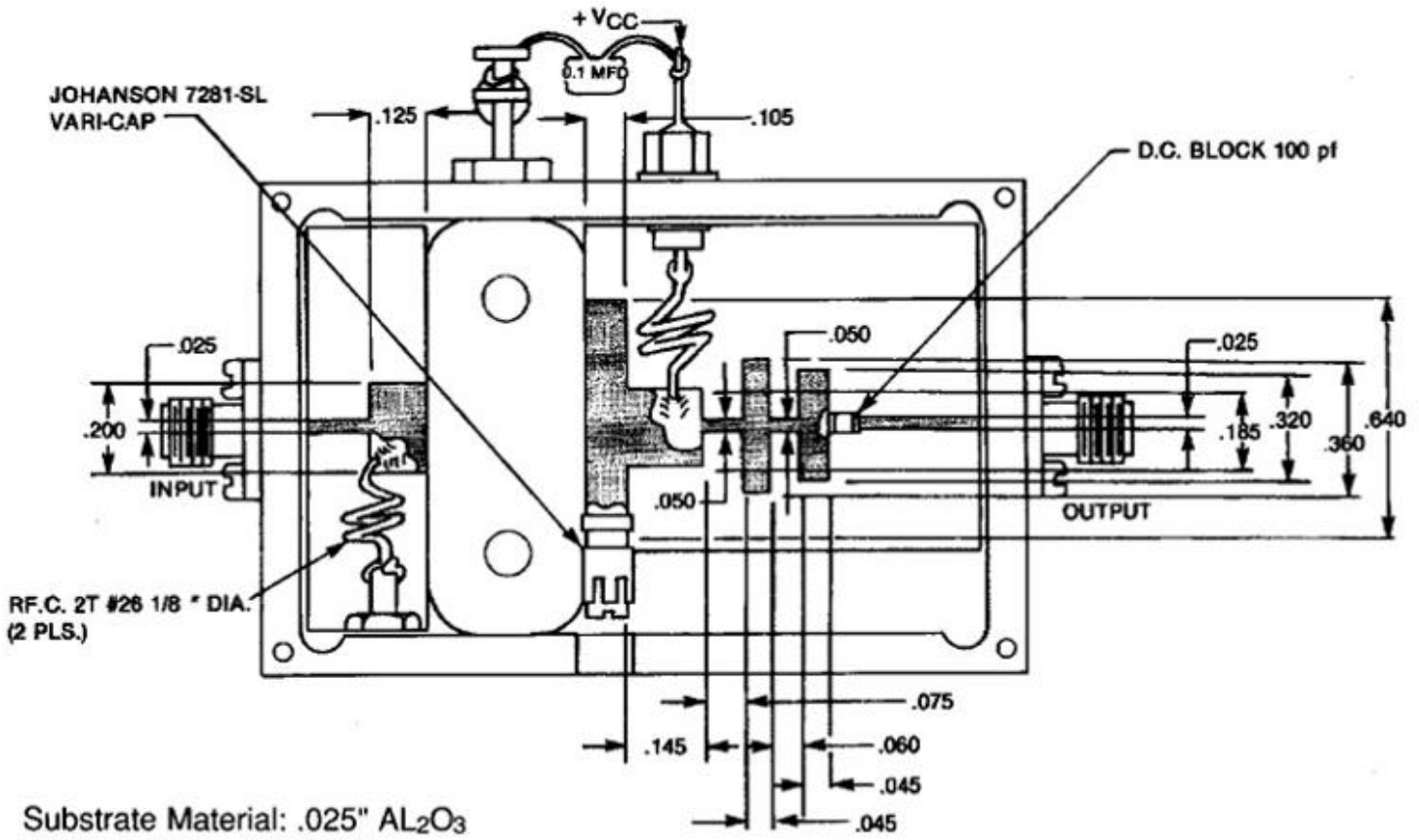
**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**
**STATIC**

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
<b>BV<sub>CBO</sub></b>	<b>I<sub>C</sub> = 5 mA</b>	<b>I<sub>E</sub> = 0 mA</b>	<b>45</b>	---	---	<b>V</b>	
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 1 mA</b>	<b>I<sub>C</sub> = 0 mA</b>	<b>3.5</b>	---	---	<b>V</b>	
<b>I<sub>CBO</sub></b>	<b>V<sub>CB</sub> = 24 V</b>		---	---	<b>2.0</b>	<b>mA</b>	
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V</b>	<b>I<sub>C</sub> = 2 A</b>	<b>30</b>	---	<b>300</b>	---	

**DYNAMIC**

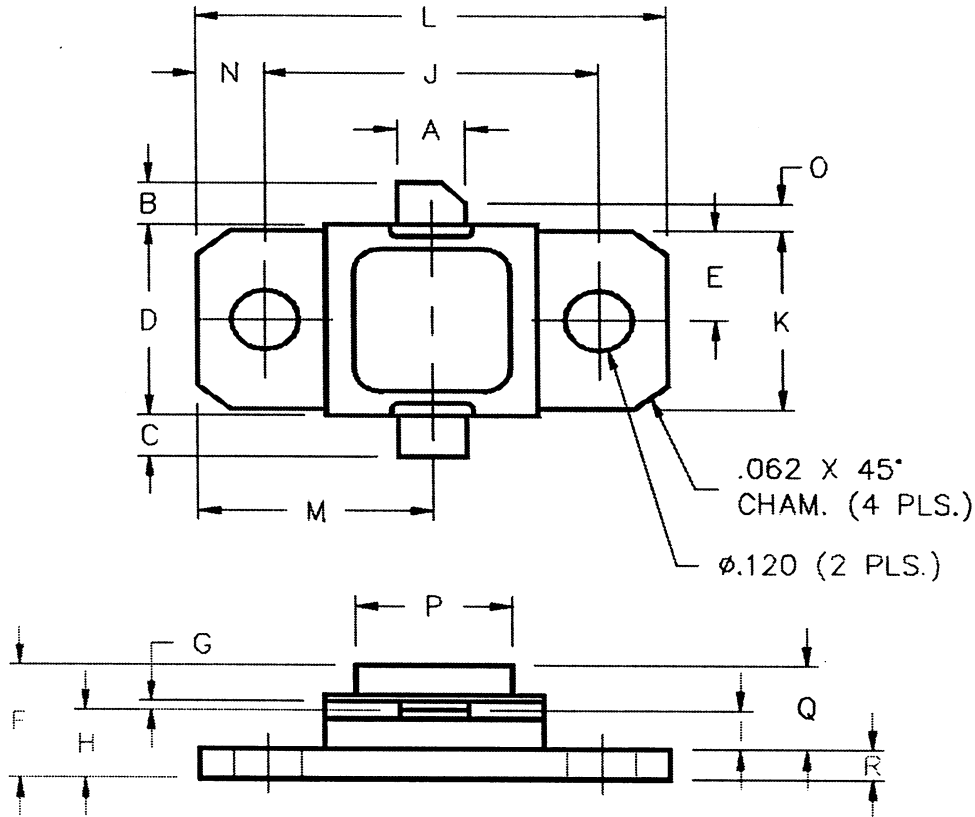
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 2.2 - 2.3 GHz</b>	<b>P<sub>IN</sub> = 4.0W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>18</b>	---	---	<b>W</b>
<b>η<sub>c</sub></b>	<b>f = 2.2 - 2.3 GHz</b>	<b>P<sub>IN</sub> = 4.0W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>40</b>	---	---	<b>%</b>
<b>G<sub>p</sub></b>	<b>f = 2.2 - 2.3 GHz</b>	<b>P<sub>IN</sub> = 4.0W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>6.5</b>	---	---	<b>dB</b>

**TEST CIRCUIT**



Substrate Material: .025"  $Al_2O_3$   
 Ref.: Dwg. No. J125199B

**PACKAGE MECHANICAL DATA**



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.140/3,56		J	.650/16,51	
B	.110/2,80		K	.386/9,80	
C	.110/2,80		L	.900/22,86	
D	.395/10,03	.407/10,34	M	.450/11,43	
E	.193/4,90		N	.125/3,18	
F		.230/5,84	O	.050/1,27	
G	.003/0,08	.006/0,15	P	.405/10,29	
H	.118/3,00	.131/3,33	Q	.170/4,32	
I	.063/1,60		R	.062/1,58	